01E 11019

7-35-25

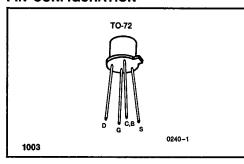
3N170, 3N171 N-Channel Enhancement **Mode MOSFET Switch**

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FEATURES

- Low Switching Voltages
- Fast Switching Times
- Low Drain-Source Resistance
- Low Reverse Transfer Capacitance

PIN CONFIGURATION



ORDERING INFORMATION

TO-72
3N170
3N171

HANDLING PRECAUTIONS

MOS field-effect transistors have extremely high input resistance and can be damaged by the accumulation of excess static charge. To avoid possible damage to the device while wiring, testing, or in actual operation, follow the procedures outlined below.

- To avoid the build-up of static charge, the leads of the devices should remain shorted together with a metal ring except when being tested or used.
- Avoid unnecessary handling. Pick up devices by the case instead of the leads.
- Do not insert or remove devices from circuits with the power on as transient voltages may cause permanent damage to the devices.

ABSOLUTE MAXIMUM RATINGS

(T _A = 25°C unless otherwise noted)
Drain-Gate Voltage ±35V
Drain-Source Voltage
Gate-Source Voltage ±35V
Drain Current 30mA
Storage Temperature Range65°C to +200°C
Operating Temperature Range55°C to +150°C
Lead Temperature (Soldering, 10sec) +300°C
Power Dissipation
Derate above 25°C 2.4mW/°C

NOTE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted) Substrate connected to source.

Symbol	Parameter		Test Conditions		Limits		Units
- Cym.501					Min	Max	Jille
BV _{DSS}	Drain-Source Breakdown Voltage		I _D =10μA, V _{GS} =0		25		V
lgss	Gate Leakage Current		V _{GS} = ±35V, V _{DS} =0			±10	рA
			V _{GS} =35V, V _{DS} =0,	T _A =125°C		100	PA
IDSS	Zero-Gate-Voltage Dr	ain Current	V _{DS} =10V, V _{GS} =0			10	nA
				T _A =125°C		1.0	μΑ
V _{GS(th)}	Gate-Source	3N170	$V_{DS} = 10V, I_D = 10\mu A$	Α	1.0	2.0	v
	Threshold Voltage	3N171		1.5	3.0	•	
I _{D(on)}	"ON" Drain Current		V _{GS} =10V, V _{DS} =10)V	10		mA
V _{DS(on)}	Drain-Source "ON" Voltage		I _D =10mA, V _{GS} =10	V		2.0	٧
rds(on)	Drain-Source ON Resistance		V _{GS} =10V, I _D =0, f=	= 1.0kHz		200	Ω

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INTERSIL

T-35-25

$\textbf{ELECTRICAL CHARACTERISTICS} \hspace{0.2cm} \textbf{(Continued)} \hspace{0.2cm} \textbf{($T_A=25^{\circ}$C unless otherwise specified)} \hspace{0.2cm} \textbf{Substrate connected to} \\$

		Tarak Com dikitoma	Limits		Units
Symbol	Parameter	Test Conditions	Min	Max	Cinto
Y _{fs}	Forward Transfer Admittance	V _{DS} =10V, I _D =2.0mA, f=1.0kHz	1000		μS
C _{rss}	Reverse Transfer Capacitance (Note 1)	V _{DS} =0, V _{GS} =0, f=1.0MHz		1.3	
Ciss	Input Capacitance (Note 1)	V _{DS} =10V, V _{GS} =0, f=1.0MHz		5.0	pF
C _{d(sub)}	Drain-Substrate Capacitance (Note 1)	V _{D(SUB)} = 10V, f = 1.0MHz		5.0	
t _{d(on)}	Turn-On Delay Time (Note 1)	$V_{DD} = 10V, I_{D(on)} = 10mA,$		3.0	
tr	Rise Time (Note 1)	$V_{GS(on)} = 10V, V_{GS(off)} = 0,$		10	ns
t _{d(off)}	Turn-Off Delay Time (Note 1)	$R_{G}=50\Omega$		3.0	
te	Fall Time (Note 1)			15	

NOTE 1: For design reference only, not 100% tested.